$SiO_2$ Etching by HF in Liquid-Like $H_2O$ Layer in a Vacuum Environment Figure Sheet

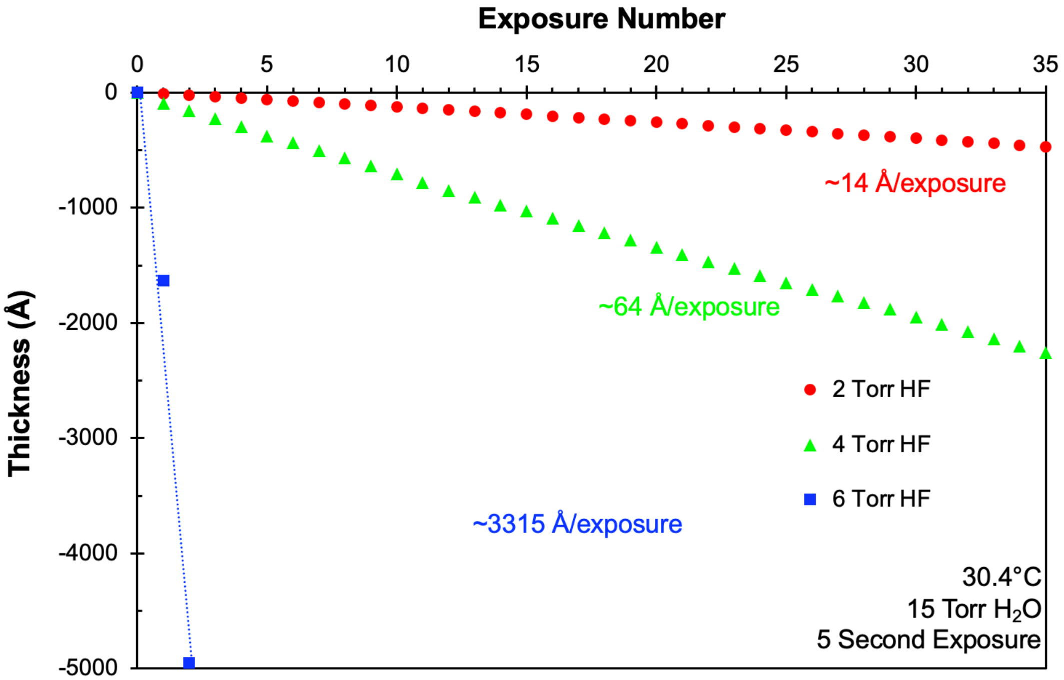

**Figure 1.** The etch rate of $SiO_2$ samples exposed to 15 Torr $H_2O$ and various HF pressures for 5 seconds at 30.4°C. As the HF pressure is increased, the etch rate increases.

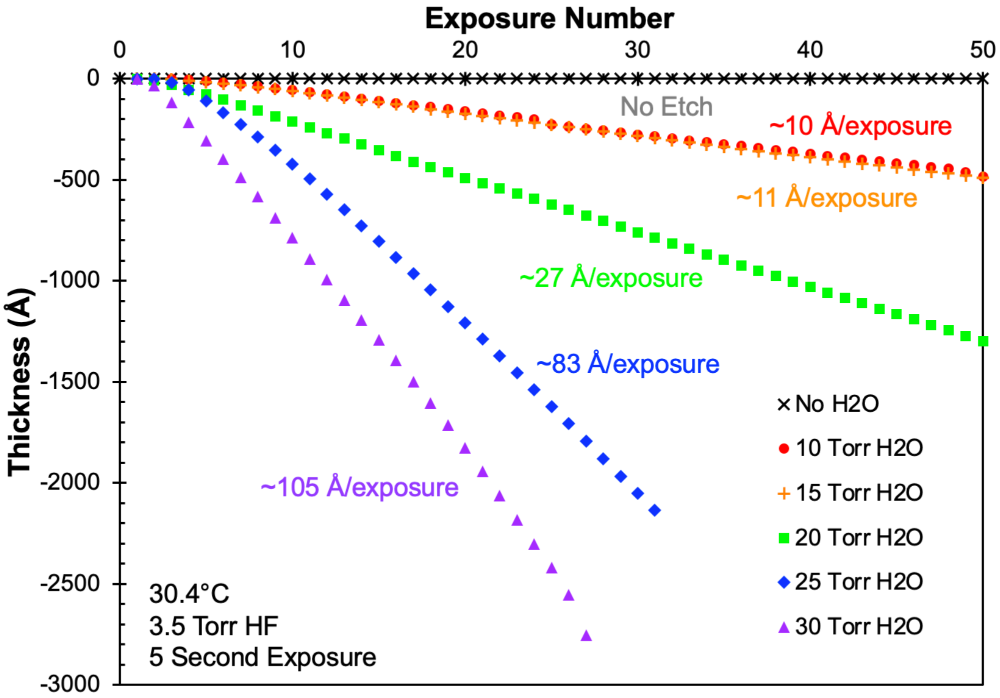

**Figure 2.** The etch rate of $SiO_2$ samples exposed to various $H_2O$ pressures and 3.5 Torr HF for 5 seconds at 30.4°C. When there is no water inside the chamber, there is no etching. As the water pressure is increased, the etch rate increases.